

Weifeng Sun

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/3970823/publications.pdf>

Version: 2024-02-01

166
papers

1,618
citations

361388

20
h-index

501174

28
g-index

166
all docs

166
docs citations

166
times ranked

910
citing authors

#	ARTICLE	IF	CITATIONS
1	Repetitive Unclamped-Inductive-Switching-Induced Electrical Parameters Degradations and Simulation Optimizations for 4H-SiC MOSFETs. IEEE Transactions on Electron Devices, 2016, 63, 4331-4338.	3.0	61
2	Comprehensive Investigations on Degradations of Dynamic Characteristics for SiC Power MOSFETs Under Repetitive Avalanche Shocks. IEEE Transactions on Power Electronics, 2019, 34, 2748-2757.	7.9	45
3	Comprehensive Analysis of Electrical Parameters Degradations for SiC Power MOSFETs Under Repetitive Short-Circuit Stress. IEEE Transactions on Electron Devices, 2018, 65, 5440-5447.	3.0	42
4	Investigations on the Degradations of Double-Trench SiC Power MOSFETs Under Repetitive Avalanche Stress. IEEE Transactions on Electron Devices, 2019, 66, 546-552.	3.0	38
5	Further Study of the U-Shaped Channel SOI-LIGBT With Enhanced Current Density for High-Voltage Monolithic ICs. IEEE Transactions on Electron Devices, 2016, 63, 1161-1167.	3.0	37
6	Electrical Characteristic Study of an SOI-LIGBT With Segmented Trenches in the Anode Region. IEEE Transactions on Electron Devices, 2016, 63, 2003-2008.	3.0	37
7	Fast Computation of Radial Vibration in Switched Reluctance Motors. IEEE Transactions on Industrial Electronics, 2018, 65, 4588-4598.	7.9	37
8	An Improved Quadrangle Control Method for Four-Switch Buck-Boost Converter With Reduced Loss and Decoupling Strategy. IEEE Transactions on Power Electronics, 2021, 36, 10827-10841.	7.9	36
9	A Low-Cost Constant Current Control Method for DCM and CCM in Digitally Controlled Primary-Side Regulation Flyback Converter. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2018, 6, 1483-1494.	5.4	31
10	A Novel Silicon-on-Insulator Lateral Insulated-Gate Bipolar Transistor With Dual Trenches for Three-Phase Single Chip Inverter ICs. IEEE Electron Device Letters, 2015, 36, 693-695.	3.9	28
11	Resonance Reduction by Optimal Switch Angle Selection in Switched Reluctance Motor. IEEE Transactions on Industrial Electronics, 2020, 67, 1867-1877.	7.9	28
12	A Two-Stage Buck-Boost Integrated LLC Converter With Extended ZVS Range and Reduced Conduction Loss for High-Frequency and High-Efficiency Applications. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2021, 9, 727-743.	5.4	28
13	A Review on Hot-Carrier-Induced Degradation of Lateral DMOS Transistor. IEEE Transactions on Device and Materials Reliability, 2018, 18, 298-312.	2.0	26
14	Repetitive-Avalanche-Induced Electrical Parameters Shift for 4H-SiC Junction Barrier Schottky Diode. IEEE Transactions on Electron Devices, 2015, 62, 601-605.	3.0	25
15	A Single-Switched High-Switching-Frequency Quasi-Resonant Flyback Converter. IEEE Transactions on Power Electronics, 2019, 34, 8775-8786.	7.9	25
16	High voltage thick SOI-LIGBT with high current density and latch-up immunity. , 2015, , .		24
17	Interfacial damage extraction method for SiC power MOSFETs based on C-V characteristics. , 2017, , .		24
18	A high current density SOI-LIGBT with Segmented Trenches in the Anode region for suppressing negative differential resistance regime. , 2015, , .		23

#	ARTICLE	IF	CITATIONS
19	Understanding Short-Circuit Failure Mechanism of Double-Trench SiC Power MOSFETs. IEEE Transactions on Electron Devices, 2020, 67, 5593-5599.	3.0	23
20	A Novel Charge-Imbalance Termination for Trench Superjunction VDMOS. IEEE Electron Device Letters, 2010, 31, 1434-1436.	3.9	22
21	Novel Digital Control Method for Improving Dynamic Responses of Multimode Primary-Side Regulation Flyback Converter. IEEE Transactions on Power Electronics, 2017, 32, 1457-1468.	7.9	22
22	Novel Snapback-Free Reverse-Conducting SOI-LIGBT With Dual Embedded Diodes. IEEE Transactions on Electron Devices, 2017, 64, 1187-1192.	3.0	21
23	Noise Immunity and its Temperature Characteristics Study of the Capacitive-Loaded Level Shift Circuit for High Voltage Gate Drive IC. IEEE Transactions on Industrial Electronics, 2018, 65, 3027-3034.	7.9	21
24	High precision constant voltage digital control scheme for primary-side controlled flyback converter. IET Power Electronics, 2016, 9, 2522-2533.	2.1	19
25	Single Pulse Unclamped-Inductive-Switching Induced Failure and Analysis for 650 V p-GaN HEMT. IEEE Transactions on Power Electronics, 2020, 35, 11328-11331.	7.9	19
26	Hot-Carrier-Induced Degradations and Optimizations for Lateral DMOS Transistor With Multiple Floating Poly-Gate Field Plates. IEEE Transactions on Electron Devices, 2017, 64, 3275-3281.	3.0	17
27	Comparison Investigations on Unclamped-Inductive-Switching Behaviors of Power GaN Switching Devices. IEEE Transactions on Industrial Electronics, 2022, 69, 5041-5049.	7.9	17
28	A capacitive-loaded level shift circuit for improving the noise immunity of high voltage gate drive IC. , 2015, , .		16
29	Implementation of a High-Precision and Wide-Range Time-to-Digital Converter With Three-Level Conversion Scheme. IEEE Transactions on Circuits and Systems II: Express Briefs, 2017, 64, 181-185.	3.0	16
30	A U-Shaped Channel SOI-LIGBT With Dual Trenches. IEEE Transactions on Electron Devices, 2017, 64, 2587-2591.	3.0	16
31	A Digital Control Scheme for PSR Flyback Converter in CCM and DCM. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2020, 8, 2837-2849.	5.4	16
32	Failure Analysis of Superjunction VDMOS Under UIS Condition. IEEE Transactions on Device and Materials Reliability, 2014, 14, 523-528.	2.0	15
33	Low-Loss SOI-LIGBT With Dual Deep-Oxide Trenches. IEEE Transactions on Electron Devices, 2017, 64, 3282-3286.	3.0	15
34	Low-Loss SOI-LIGBT With Triple Deep-Oxide Trenches. IEEE Transactions on Electron Devices, 2017, 64, 3756-3761.	3.0	15
35	Digital regulation scheme for multimode primary-side controlled flyback converter. IET Power Electronics, 2016, 9, 782-788.	2.1	14
36	An Integrated Bootstrap Diode Emulator for 600-V High Voltage Gate Drive IC With P-Sub/P-Epi Technology. IEEE Transactions on Power Electronics, 2016, 31, 518-523.	7.9	14

#	ARTICLE	IF	CITATIONS
37	A digital detecting method for synchronous rectification based on dual-verification for LLC resonant converter. , 2018, , .		14
38	A Novel Lateral DMOS Transistor With H-Shape Shallow-Trench-Isolation Structure. IEEE Transactions on Electron Devices, 2018, 65, 5218-5221.	3.0	14
39	Sampled-Data Modeling for PCM and ZVS Controlled Critical Conduction Mode (CrCM) Active Clamp Flyback (ACF) Converter at Variable Switching Frequency. IEEE Transactions on Circuits and Systems I: Regular Papers, 2020, 67, 3588-3600.	5.4	14
40	Electrical Characteristic Investigation on a Novel Double-Well Isolation Structure in 600-V-Class High-Voltage Integrated Circuits. IEEE Transactions on Electron Devices, 2012, 59, 3477-3481.	3.0	13
41	Investigation on degradation mechanism and optimization for SiC power MOSFETs under long-term short-circuit stress. , 2018, , .		13
42	Single-Pulse Avalanche Failure Investigations of Si-SJ-mosfet and SiC-mosfet by Step-Control Infrared Thermography Method. IEEE Transactions on Power Electronics, 2020, 35, 5180-5189.	7.9	13
43	Hot-Carrier-Induced On-Resistance Degradation of n-Type Lateral DMOS Transistor With Shallow Trench Isolation for High-Side Application. IEEE Transactions on Device and Materials Reliability, 2015, 15, 458-460.	2.0	12
44	Influence of switch angles on second-order current harmonic and resonance in switched reluctance motors. IET Electric Power Applications, 2018, 12, 1247-1255.	1.8	12
45	Small Signal Modeling and Control Loop Design of Critical Conduction Mode Active Clamp Flyback Converter. IEEE Transactions on Power Electronics, 2021, 36, 7250-7263.	7.9	12
46	Simulation Study of A 1200V 4H-SiC Lateral MOSFET With Reduced Saturation Current. IEEE Electron Device Letters, 2021, 42, 1037-1040.	3.9	12
47	TC-LIGBTs on the Thin Sol Layer for the High Voltage Monolithic ICs With High Current Density and Latch-Up Immunity. IEEE Transactions on Electron Devices, 2014, 61, 3814-3820.	3.0	11
48	Investigation on Self-Adjust Conductivity Modulation SOI-LIGBT Structure (SCM-LIGBT) for Monolithic High-Voltage IC. IEEE Transactions on Electron Devices, 2017, 64, 3762-3767.	3.0	11
49	Lateral DMOS With Partial-Resist-Implanted Drift Region for Alleviating Hot-Carrier Effect. IEEE Transactions on Device and Materials Reliability, 2017, 17, 780-784.	2.0	11
50	Turn-Off Transient of Superjunction SOI Lateral IGBTs: Mechanism and Optimization Strategy. IEEE Transactions on Electron Devices, 2019, 66, 1409-1415.	3.0	11
51	500-V Silicon-On-Insulator Lateral IGBT With W-Shaped n-Typed Buffer and Composite p-Typed Collectors. IEEE Transactions on Electron Devices, 2019, 66, 1430-1434.	3.0	11
52	A New Modulation Strategy for Four-switch Buck-boost Converter with Reduced Freewheeling Current. , 2020, , .		11
53	Super Field Plate Technique That Can Provide Charge Balance Effect for Lateral Power Devices Without Occupying Drift Region. IEEE Transactions on Electron Devices, 2020, 67, 2218-2222.	3.0	11
54	Novel Hot-Carrier Degradation Mechanisms in the Lateral Insulated-Gate Bipolar Transistor on SOI Substrate. IEEE Transactions on Electron Devices, 2011, 58, 1158-1163.	3.0	10

#	ARTICLE	IF	CITATIONS
55	A Phase-Shift Triple Full-Bridge Converter With Three Shared Leading Legs. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2018, 6, 1912-1920.	5.4	10
56	Verification of Single-Pulse Avalanche Failure Mechanism for Double-Trench SiC Power MOSFETs. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2021, 9, 2190-2200.	5.4	10
57	High-Voltage a-IGZO TFTs With the Stair Gate-Dielectric Structure. IEEE Transactions on Electron Devices, 2021, 68, 4462-4466.	3.0	10
58	Electrical performances degradations and physics based mechanisms under negative bias temperature instability stress for p-GaN gate high electron mobility transistors. Semiconductor Science and Technology, 2021, 36, 014007.	2.0	10
59	Comparisons of hot-carrier degradation behavior in SOI-LIGBT and SOI-LDMOS with different stress conditions. Solid-State Electronics, 2010, 54, 1598-1601.	1.4	9
60	Off-State Stress Degradation Analysis and Optimization for the High-Voltage SOI-pLED MOS With Thick Gate Oxide. IEEE Transactions on Electron Devices, 2013, 60, 3632-3638.	3.0	9
61	A noise immunity improved level shift structure for a 600 V HVIC. Journal of Semiconductors, 2013, 34, 065008.	3.7	9
62	A High-Frequency Model for a PCM Buck Converter. IEEE Transactions on Power Electronics, 2015, 30, 2304-2312.	7.9	9
63	Electrical Parameters Degradations and Optimizations of SOI-LIGBT Under Repetitive Unclamped-Inductive-Switching Conditions. IEEE Transactions on Electron Devices, 2016, 63, 1644-1649.	3.0	9
64	Analysis of a Time-Length Compensation Algorithm for Elimination of Subharmonic Oscillation and Application in a Digitally Controlled Primary-Side Regulation Flyback Converter. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2017, 5, 1710-1719.	5.4	9
65	Optimization of V_{CE} Plateau for Deep-Oxide Trench SOI Lateral IGBT During Inductive Load Turn-OFF. IEEE Transactions on Electron Devices, 2018, 65, 3862-3868.	3.0	9
66	Mechanism and Novel Structure for di/dt Controllability in U-Shaped Channel Silicon-on-Insulator Lateral IGBTs. IEEE Electron Device Letters, 2019, 40, 1658-1661.	3.9	9
67	Complete Avalanche Process and Failure Mechanism of Trench-Gate FS-IGBT Under Unclamped Inductive Switching by Using Infrared Visualization Method. IEEE Transactions on Electron Devices, 2020, 67, 3908-3911.	3.0	9
68	Investigations on Electrical Parameters Degradations of p-GaN HEMTs Under Repetitive UIS Stresses. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2021, 9, 2227-2234.	5.4	9
69	Investigation on the Degradation Mechanism for SiC Power MOSFETs Under Repetitive Switching Stress. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2021, 9, 2180-2189.	5.4	9
70	A Novel Digital Control Method of Primary-Side Regulated Flyback With Active Clamping Technique. IEEE Transactions on Circuits and Systems I: Regular Papers, 2021, 68, 950-962.	5.4	9
71	A Robust W-Shape-Buffer LIGBT Device With Large Current Capability. IEEE Transactions on Power Electronics, 2014, 29, 4466-4469.	7.9	8
72	Layout Arrangement Concern for Lateral DMOS With Large Geometric Array Used as Output Device. IEEE Transactions on Device and Materials Reliability, 2017, 17, 450-457.	2.0	8

#	ARTICLE	IF	CITATIONS
73	Comprehensive Investigation on Electrical Properties of nLDMOS and pLDMOS Under Mechanical Strain. IEEE Transactions on Electron Devices, 2019, 66, 1012-1017.	3.0	8
74	Reliability Concern of 650-V Normally-OFF GaN Devices Under Reverse Freewheeling Stress. IEEE Transactions on Electron Devices, 2020, 67, 3492-3495.	3.0	8
75	High-temperature electrical performances and physics-based analysis of p-GaN HEMT device. IET Power Electronics, 2020, 13, 420-425.	2.1	8
76	Modeling Avalanche Induced Degradation for 4H-SiC Power MOSFETs. IEEE Transactions on Power Electronics, 2020, 35, 11299-11303.	7.9	8
77	An Improved Adaptive Synchronous Rectification Method with the Enhanced Capacity to Eliminate Reverse Current. IEEE Transactions on Power Electronics, 2021, , 1-1.	7.9	8
78	An accurate design method of RCD circuit for flyback converter considering diode reverse recovery. , 2016, , .		7
79	A new high-voltage interconnection shielding method for SOI monolithic ICs. Solid-State Electronics, 2017, 133, 25-30.	1.4	7
80	Turn-off failure in multi-finger SOI-LIGBT used for single chip inverter ICs. Solid-State Electronics, 2017, 137, 29-37.	1.4	7
81	A simple average current control with time-length equality for primary-side regulation flyback converter with constant output current control. International Journal of Circuit Theory and Applications, 2018, 46, 2477-2494.	2.0	7
82	A Wide Dynamic Range and Low Bit Error Pixel TDC Suitable for Array Application. IEEE Transactions on Circuits and Systems II: Express Briefs, 2019, 66, 1805-1809.	3.0	7
83	Study and Implementation of 600-V High-Voltage Gate Driver IC With the Common-Mode Dual-Interlock Technique for GaN Devices. IEEE Transactions on Industrial Electronics, 2021, 68, 1506-1514.	7.9	7
84	An Autotuning Method Based on System Identification for Digitally Controlled Synchronous Buck Converter. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2021, 9, 3307-3321.	5.4	7
85	Anomalous output characteristic shift for the n-type lateral diffused metal-oxide-semiconductor transistor with floating P-top layer. Applied Physics Letters, 2014, 104, .	3.3	6
86	Investigation on Hot-Carrier-Induced degradation of STI-nLDMOS with two-step-oxide process for high side application. , 2016, , .		6
87	Comparison of short-circuit characteristics of trench gate and planar gate U-shaped channel SOI-LIGBTs. Solid-State Electronics, 2017, 135, 24-30.	1.4	6
88	U-shaped channel SOI-LIGBT with dual trenches to improve the trade-off between saturation voltage and turn-off loss. , 2017, , .		6
89	Extraction method of interfacial injected charges for SiC power MOSFETs. Superlattices and Microstructures, 2018, 113, 706-712.	3.1	6
90	Comparative Study on Vibration Mode with Different Current Amplitudes and Modeling of Radial Vibration in Switched Reluctance Motor. , 2018, , .		6

#	ARTICLE	IF	CITATIONS
91	Comprehensive investigation on mechanical strain induced performance boosts in LDMOS. , 2018, , .		6
92	Experimental Investigation on the Electrical Properties of Lateral IGBT Under Mechanical Strain. IEEE Electron Device Letters, 2019, 40, 937-940.	3.9	6
93	Reliability Concerns on LDMOS With Different Split-STI Layout Patterns. IEEE Transactions on Electron Devices, 2020, 67, 185-192.	3.0	6
94	Quasisaturation Effect and Optimization for 4H-SiC Trench MOSFET With P+ Shielding Region. IEEE Transactions on Electron Devices, 2021, 68, 4550-4556.	3.0	6
95	Understanding Electrical Parameter Degradations of P-GaN HEMT Under Repetitive Short-Circuit Stresses. IEEE Transactions on Power Electronics, 2021, 36, 12173-12176.	7.9	6
96	Zero-steady-state-error compensation method in application of peak current mode buck converter with fast transient response. IET Power Electronics, 2015, 8, 647-655.	2.1	5
97	OFF-State Inrush-Current-Induced Electrical Parameter Degradations for High-Voltage Lateral DMOS Transistors. IEEE Transactions on Electron Devices, 2015, 62, 3767-3773.	3.0	5
98	Hot-Carrier-Induced Degradations Investigations for 600 V SOI-LIGBT by an Improved Charge Pumping Solution. IEEE Transactions on Electron Devices, 2017, 64, 634-637.	3.0	5
99	Mobility Fluctuation-Induced Low-Frequency Noise in Ultrascaled Ge Nanowire nMOSFETs With Near-Ballistic Transport. IEEE Transactions on Electron Devices, 2018, 65, 2573-2577.	3.0	5
100	Influence of Latch-Up Immunity Structure on ESD Robustness of SOI-LIGBT Used As Output Device. IEEE Transactions on Device and Materials Reliability, 2018, 18, 284-290.	2.0	5
101	An Integrated Bias Voltage Control Method for SPAD Arrays. IEEE Photonics Technology Letters, 2018, 30, 1723-1726.	2.5	5
102	Switch-OFF Avalanche-Breakdown-Induced Electrical Degradations of RF-LDMOS Transistor for SMPAs Applications. IEEE Transactions on Electron Devices, 2018, 65, 4719-4723.	3.0	5
103	Hot-Carrier-Induced Degradation and Optimization for 700-V High-Voltage Lateral DMOS by the AC Stress. IEEE Transactions on Electron Devices, 2020, 67, 1090-1097.	3.0	5
104	New Digital Control Method for Improving Dynamic Response of Synchronous Rectified PSR Flyback Converter With CCM and DCM Modes. IEEE Transactions on Power Electronics, 2020, 35, 12347-12358.	7.9	5
105	New Failure Mechanism Induced by Current Limit for Superjunction MOSFET Under Single-Pulse UIS Stress. IEEE Transactions on Electron Devices, 2021, 68, 3483-3489.	3.0	5
106	Silicon-on-Insulator Lateral DMOS With Potential Modulation Plates and Multiple Deep-Oxide Trenches. IEEE Transactions on Electron Devices, 2021, 68, 5073-5077.	3.0	5
107	A Silicon-On-Insulator Lateral IGBT With Segmented Trenches for Improving Short-Circuit Withstanding Capability. IEEE Transactions on Electron Devices, 2022, 69, 4042-4045.	3.0	5
108	400-V Amorphous IGZO Thin-Film Transistors With Drift Region Doped by Hydrogen. IEEE Transactions on Electron Devices, 2022, 69, 3732-3736.	3.0	5

#	ARTICLE	IF	CITATIONS
109	A novel digital multi-mode control strategy with PSM for primary-side flyback converter. International Journal of Electronics, 2017, 104, 840-854.	1.4	4
110	Fast recovery SOI PiN diode with multiple trenches. Superlattices and Microstructures, 2017, 111, 405-413.	3.1	4
111	A high-speed SOI-LIGBT with electric potential modulation trench and low-doped buried layer. , 2018, , .		4
112	Reliability concern of quasi-vertical GaN Schottky barrier diode under high temperature reverse bias stress. Superlattices and Microstructures, 2019, 130, 233-240.	3.1	4
113	Breakdown Voltage Walk-in Phenomenon and Optimization for the Trench-Gate p-Type VDMOS Under Single Avalanche Stress. IEEE Transactions on Electron Devices, 2020, 67, 2445-2450.	3.0	4
114	Investigation on the Degradation Mechanism for GaN Cascode Device Under Repetitive Hard-Switching Stress. IEEE Transactions on Power Electronics, 2022, 37, 6009-6017.	7.9	4
115	High Precision Primary Side Regulation Constant Voltage Control Method for Primary and Secondary Resonant Active Clamp Flyback Converter. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2022, 10, 6985-6999.	5.4	4
116	A review on recent effort of conductive EMI suppression methods in high-frequency power converters. IET Power Electronics, 2022, 15, 1921-1935.	2.1	4
117	Hot-carrier degradation mechanism for p-type symmetric LDMOS transistor with thick gate oxide. Electronics Letters, 2012, 48, 1545-1546.	1.0	3
118	Reliability concern and design for the lateral insulator gate bipolar transistor based on SOI substrate. Solid-State Electronics, 2013, 85, 28-35.	1.4	3
119	A <i>LLC</i> resonant converter with dual resonant frequency for high light load efficiency. International Journal of Electronics, 0, , 1-15.	1.4	3
120	Study on EMI Characteristics of the Superjunction DMOS in Flyback Converter System. IEEE Transactions on Device and Materials Reliability, 2017, 17, 692-697.	2.0	3
121	Integrated GaN MIS-HEMT with Multi-Channel Heterojunction SBD Structures. , 2019, , .		3
122	Analog Compensator Design for Half Bridge LLC Resonant Converter. , 2019, , .		3
123	Hot-Carrier-Induced Degradation and Optimization for Lateral DMOS With Split-STI-Structure in the Drift Region. IEEE Transactions on Electron Devices, 2019, 66, 2869-2875.	3.0	3
124	Experimental Investigation on the Electrical Properties of SOI-LIGBT Under Total-Ionizing-Dose Radiation. , 2020, , .		3
125	Design and implementation of a hybrid DPWM under 50 ps resolution based on general-purpose FPGA. International Journal of Circuit Theory and Applications, 2021, 49, 114-127.	2.0	3
126	System Performance Optimization for Dual-Loop Dual-Variable Controlled Active Clamp Flyback Converter Using Decoupling Compensation Technique. , 2021, , .		3

#	ARTICLE	IF	CITATIONS
127	Performance Boosts in n-Type Lateral Double-Diffused MOSFET With Process-Induced Strain Using Contact Etch Stop Layer Stressor. IEEE Transactions on Electron Devices, 2021, 68, 421-424.	3.0	3
128	Comprehensive Investigation on Electrical Properties of Split-Gate Trench Power MOSFETs Under Mechanical Strains. IEEE Transactions on Electron Devices, 2022, 69, 1191-1195.	3.0	3
129	Numerical study of a novel GaN vertical FinFET with a p-base structure for high switching performance. Journal of Computational Electronics, 2022, 21, 625-632.	2.5	3
130	Unclamped-Inductive-Switching Behaviors of p-GaN HEMTs at Cryogenic Temperature. IEEE Transactions on Power Electronics, 2022, 37, 11507-11510.	7.9	3
131	Duty-cycle-accelerated hot-carrier degradation and lifetime evaluation for 700V lateral DMOS. , 2018, , .		2
132	Lightning Surge Robustness Analysis and Optimization for an LED Driver Based on a Flyback Converter. IEEE Transactions on Industrial Electronics, 2021, 68, 10449-10458.	7.9	2
133	Experimental investigation on total-ionizing-dose radiation effects on the electrical properties of SOI-LIGBT. Solid-State Electronics, 2021, 175, 107952.	1.4	2
134	Numerical Study of Novel GaN HEMTs With Integrated SBDs for Ultrahigh Reverse Conduction Capability. IEEE Transactions on Electron Devices, 2021, 68, 931-933.	3.0	2
135	Hot-Carrier-Induced Reliability Concerns for Lateral DMOS Transistors with Split-STI Structures. , 2021, , .		2
136	Simulation Study of Novel Trench Gate U-Shaped Channel SOI Lateral IGBTs With Suppressed Gate Voltage Overshoot and Reduced $\frac{di}{dt}$. IEEE Transactions on Electron Devices, 2021, 68, 3930-3935.	3.0	2
137	Novel Multiple-Layer Stack Capacitor and Its Application in the IRPFA Readout Circuit. IEEE Access, 2021, 9, 161806-161813.	4.2	2
138	An Improved Peak Current Control Method for GaN-based Active-clamped Flyback Converter. , 2020, , .		2
139	A Digital Adaptive Control Method for Optimizing Valley Current of Active Clamp Flyback Converter. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2022, 10, 5749-5761.	5.4	2
140	High-Voltage Electron Injection Enhanced TC-LIGBT on 1.5- μm -Thin SOI Layer for Reducing the Forward Voltage Drop. IEEE Transactions on Electron Devices, 2016, 63, 4873-4879.	3.0	1
141	A time-length compensation algorithm for sub-harmonic oscillation elimination in digital controlled primary-side regulation flyback converter. , 2017, , .		1
142	Analysis of clamped inductive turn-off failure of multi-finger lateral IGBT in SOI single chip inverter ICs. , 2017, , .		1
143	Analysis and optimization of the switching noise for Super-junction MOSFET in full bridge converter system. Solid-State Electronics, 2019, 161, 107638.	1.4	1
144	Small-signal modelling for time-length compensation algorithm in current controlled converters. International Journal of Circuit Theory and Applications, 2020, 48, 148-155.	2.0	1

#	ARTICLE	IF	CITATIONS
145	Analysis of OFF-state dynamic avalanche instability in silicon-on-insulator lateral IGBTs at low temperature. <i>Microelectronics Reliability</i> , 2020, 107, 113600.	1.7	1
146	A self-adaptive pulse generator to realize extremely low power consumption and high reliability of high voltage gate driver IC. <i>Analog Integrated Circuits and Signal Processing</i> , 2020, 105, 13-20.	1.4	1
147	An Ultraviolet Photon Counting Imaging System Based on a SiC SPAD Array. <i>IEEE Photonics Technology Letters</i> , 2021, 33, 1213-1216.	2.5	1
148	Experimental Investigations on the Electrical Properties of 4H-SiC Power MOSFETs Under Biaxial and Uniaxial Mechanical Strains. <i>IEEE Transactions on Power Electronics</i> , 2022, 37, 55-58.	7.9	1
149	Hot-Carrier-Induced Reliability for Lateral DMOS Transistors With Split-STI Structures. <i>IEEE Journal of the Electron Devices Society</i> , 2021, 9, 1188-1193.	2.1	1
150	Influence of Different Device Structures on the Degradation for Trench-Gate SiC MOSFETs: Taking Avalanche Stress as an Example. <i>Materials</i> , 2022, 15, 457.	2.9	1
151	Fast Transient Response Based on Single-cycle Charge Regulator (SCCR) Control to Realize Fast Recovery Process. , 2021, , .		1
152	Experimental Investigation of Dual-Gate LDMOS for Low On-Resistance. , 2022, , .		1
153	Failure Analysis and Improvement for High Power Single-Phase Module. <i>IEEE Transactions on Device and Materials Reliability</i> , 2017, 17, 170-175.	2.0	0
154	Endurance degradation and lifetime model of p-channel floating gate flash memory device with 2T structure. <i>Solid-State Electronics</i> , 2017, 134, 58-64.	1.4	0
155	Anomalous output characteristics shrinkage in STI-LDMOS transistor after repetitive I-V scanning measurements. <i>Superlattices and Microstructures</i> , 2019, 128, 204-211.	3.1	0
156	Repetitive-avalanche-induced Electrical Degradation and Optimization for 1.2kV 4H-SiC MOSFETs. , 2019, , .		0
157	A 600V PiN diode with partial recessed anode and double-side Schottky engineering for fast reverse recovery. <i>Superlattices and Microstructures</i> , 2019, 128, 56-66.	3.1	0
158	Integrated 100 V bootstrap diode with enhanced reverse recovery characteristics for eGaN field effect transistor gate drivers. <i>Electronics Letters</i> , 2020, 56, 308-309.	1.0	0
159	Comprehensive Investigation on Electrical Properties of 4H-SiC VDMOS Under Uniaxial and Biaxial Mechanical Strains. , 2021, , .		0
160	Half Bridge LLC resonant Converter Design for Wide Input Voltage Range Applications. , 2021, , .		0
161	Device and Circuit Design for Improving the Freewheeling Characteristics of High Voltage Monolithic Integrated Circuit. <i>IEEE Transactions on Industrial Electronics</i> , 2021, 68, 11420-11427.	7.9	0
162	Single Pulse Short-Circuit Failure Mechanism of 1200V Asymmetric Trench SiC MOSFETs. , 2021, , .		0

#	ARTICLE	IF	CITATIONS
163	A high-speed single-photon detection scheme based on frequency domain filtering. Measurement Science and Technology, 0, , .	2.6	0
164	Investigations on Unclamped-Inductive-Switching Behaviors of p-GaN HEMTs at Cryogenic Temperature. , 2022, , .		0
165	A High-voltage Silicon-On-Insulator Lateral IGBT with Segmented Trenches for Improved Short circuit Ruggedness. , 2022, , .		0
166	A novel high-frequency floating resonant gate driver with reduced gate driving loss. IET Power Electronics, 0, , .	2.1	0